

SCCS029 - May 1994 - Revised March 2000

8-Bit Buffers/Line Drivers

Features

- Function, pinout, and drive compatible with FCT and F logic
- FCT-C speed at 4.1 ns max. (Com'l) FCT-A speed at 4.8 ns max. (Com'l)
- Reduced V_{OH} (typically = 3.3V) versions of equivalent FCT functions
- Edge-rate control circuitry for significantly improved noise characteristics
- · Power-off disable feature
- ESD > 2000V
- · Matched rise and fall times
- Fully compatible with TTL input and output logic levels
- Sink current
 Source current
 64 mA (Com'l), 48 mA (Mil)
 32 mA (Com'l), 12 mA (Mil)

Extended commercial range of –40°C to +85°C

The outputs are designed with a power-off disable feature to allow for live insertion of boards.

and CMOS devices without external components.

The FCT540T inverting buffer/line driver and the FCT541T

non-inverting buffer/line driver are designed to be employed as

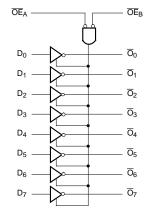
memory address drivers, clock drivers, and bus-oriented

transmitters/receivers. The devices provide speed and drive capabilities equivalent to their fastest bipolar logic

counterparts while reducing power dissipation. The input and

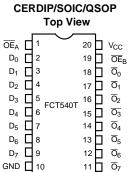
output voltage levels allow direct interface with TTL, NMOS,

Logic Block Diagram—FCT540T

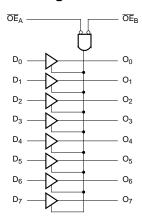


Pin Configurations

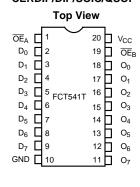
Functional Description



Logic Block Diagram—FCT541T



CERDIP/DIP/SOIC/QSOP



Function Table FCT540T^[1]

	Inputs		
OEA	OE _B	D	Output
L	L	L	Н
L	L	Н	L
H	H	X	Z

Function Table FCT541T[1]

	Inputs		
OEA	OE _B	D	Output
L	L	L	L
L	L	Н	Н
Н	Н	X	Z

Maximum Ratings^[2, 3]

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature	. –65°C to +150°C
Ambient Temperature with Power Applied	. –65°C to +135°C
Supply Voltage to Ground Potential	–0.5V to +7.0V
DC Input Voltage	–0.5V to +7.0V
DC Output Voltage	–0.5V to +7.0V
DC Output Current (Maximum Sink Current	t/Pin) 120 mA
Power Dissipation	0.5W
Static Discharge Voltage(per MIL-STD-883, Method 3015)	>2001V

Operating Range

Range	Range	Ambient Temperature	v _{cc}
Commercial	T, AT, CT	–40°C to +85°C	5V ± 5%
Military ^[4]	All	–55°C to +125°C	5V ± 10%

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Condition	Min.	Typ. ^[5]	Max.	Unit	
V _{OH}	Output HIGH Voltage	$V_{CC} = Min., I_{OH} = -32 \text{ mA}$	Com'l	2.0			V
		$V_{CC} = Min., I_{OH} = -15 \text{ mA}$	Com'l	2.4	3.3		V
		$V_{CC} = Min., I_{OH} = -12 \text{ mA}$	Mil	2.4	3.3		V
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 64 mA	Com'l		0.3	0.55	V
		V _{CC} = Min., I _{OL} = 48 mA	Mil		0.3	0.55	V
V _{IH}	Input HIGH Voltage			2.0			V
V _{IL}	Input LOW Voltage					0.8	V
V _H	Hysteresis ^[6]	All inputs			0.2		V
V _{IK}	Input Clamp Diode Voltage	$V_{CC} = Min., I_{IN} = -18 \text{ mA}$			-0.7	-1.2	V
I	Input HIGH Current	$V_{CC} = Max., V_{IN} = V_{CC}$				5	μΑ
I _{IH}	Input HIGH Current	$V_{CC} = Max., V_{IN} = 2.7V$				±1	μΑ
I _{IL}	Input LOW Current	$V_{CC} = Max., V_{IN} = 0.5V$				±1	μΑ
I _{OZH}	Off State HIGH-Level Output Current	$V_{CC} = Max., V_{OUT} = 2.7V$				10	μА
I _{OZL}	Off State LOW-Level Output Current	$V_{CC} = Max., V_{OUT} = 0.5V$				-10	μΑ
Ios	Output Short Circuit Current ^[7]	$V_{CC} = Max, V_{OUT} = 0.0V$		-60	-120	-225	mA
I _{OFF}	Power-Off Disable	V _{CC} = 0V, V _{OUT} = 4.5V				±1	μΑ

Notes:

- H = HIGH Voltage Level
 L = LOW Voltage Level
 X = Don't Care
 Z = High Impedance
- Unless otherwise noted, these limits are over the operating free-air temperature range.

 Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.
- T_A is the "instant on" case temperature.
- Typical values are at V_{CC} =5.0V, T_A =+25°C ambient.
- This parameter is specified but not tested.

 Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parametric tests. In any sequence of parametric tests, I_{OS} tests should be performed last.

Capacitance^[6]

Parameter	Description	Test Conditions	Typ. ^[5]	Max.	Unit
C _{IN}	Input Capacitance		5	10	pF
C _{OUT}	Output Capacitance		9	12	pF

Power Supply Characteristics

Parameter	Description	Test Conditions	Typ. ^[5]	Max.	Unit
I _{CC}	Quiescent Power Supply Current	V_{CC} =Max., $V_{IN} \le 0.2V$, $V_{IN} \ge V_{CC}$ -0.2V	0.1	0.2	mA
Δl _{CC}	Quiescent Power Supply Current (TTL inputs)	$V_{CC} = Max., V_{IN} = 3.4V, f_1 = 0, Outputs Open^{[8]}$	0.5	2.0	mA
I _{CCD}	Dynamic Power Supply Current ^[9]	V_{CC} = Max., 50% Duty Cycle, Outputs Open, One Bit Toggling at f ₁ = 10 MHz, \overline{OE}_A = \overline{OE}_B =GND, or \overline{OE}_A =GND, \overline{OE}_B = V_{CC} , $V_{IN} \le 0.2 V$ or $V_{IN} \ge V_{CC}$ =0.2 V	0.06	0.12	mA/MHz
Ic	Total Power Supply Current ^[10]	V_{CC} =Max., 50% Duty Cycle, Outputs Open, One Bit Toggling at f ₁ =10 MHz, \overline{OE}_A = \overline{OE}_B =GND, or \overline{OE}_A =GND, \overline{OE}_B = V_{CC} , V_{IN} ≤0.2V or V_{IN} ≥ V_{CC} -0.2V	0.7	1.4	mA
		V_{CC} = Max., 50% Duty Cycle, Outputs Open, One Bit Toggling at f ₁ =10 MHz, \overline{OE}_A = \overline{OE}_B =GND, or \overline{OE}_A =GND, \overline{OE}_B = V_{CC} , V_{IN} = 3.4V or V_{IN} = GND	1.0	2.4	mA
		$\begin{array}{ c c c c c c }\hline V_{CC} = \text{Max., } 50\% \text{ Duty Cycle, Outputs Open,}\\ \hline \text{Eight Bits Toggling at } f_1 = 2.5 \text{ MHz,}\\ \hline OE_A = \overline{OE}_B = \text{GND, or } \overline{OE}_A = \text{GND, } OE_B = V_{CC,}\\ V_{IN} \leq 0.2 \text{V or } V_{IN} \geq V_{CC} - 0.2 \text{V} \end{array}$	1.3	2.6 ^[11]	mA
		V_{CC} = Max., 50% Duty Cycle, Outputs Open, Eight Bits Toggling at f_1 =2.5 MHz, \overline{OE}_A = \overline{OE}_B =GND, or \overline{OE}_A =GND, OE_B = V_{CC} , V_{IN} = 3.4V or V_{IN} = GND	3.3	10.6 ^[11]	mA

Notes:

- Per TTL driven input (V_{IN}=3.4V); all other inputs at V_{CC} or GND.
- Per TTL driven input (V_{IN} =3.4V); all other inputs at V_{CC} or GND. This parameter is not directly testable, but is derived for use in Total Power Supply calculations. $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$ $I_C = I_{CC} + \Delta I_{CC} D_H N_T + I_{CC} (f_0/2 + f_1 N_1)$ $I_{CC} = Quiescent Current with CMOS input levels <math>\Delta I_{CC} = Power Supply Current for a TTL HIGH input (<math>V_{IN}$ =3.4V) $D_H = Duty Cycle for TTL inputs HIGH <math>N_T = Number of TTL inputs at D_H$ $I_{CCD} = Dynamic Current caused by an input transition pair (HLH or LHL) <math>I_{CCD} = I_{CD} = I_{$
- - Input signal frequency
 - Number of inputs changing at f₁
- All currents are in milliamps and all frequencies are in megahertz.

 11. Values for these conditions are examples of the I_{CC} formula. These limits are specified but not tested.

Switching Characteristics Over the Operating Range^[12]

		FCT540T/FCT541T		FCT540AT/FCT541AT			
		Comme	ercial	Commercial			
Parameter	Description	Min.	Max.	Min.	Max.	Unit	Fig. No. ^[13]
t _{PLH} t _{PHL}	Propagation Delay Data to Output (FCT540)	1.5	8.5	1.5	4.8	ns	1, 2
t _{PLH} t _{PHL}	Propagation Delay Data to Output (FCT541)	1.5	8.0	1.5	4.8	ns	1, 3
t _{PZH} t _{PZL}	Output Enable Time	1.5	10.0	1.5	6.2	ns	1, 7, 8
t _{PHZ}	Output Disable Time	1.5	9.5	1.5	5.6	ns	1, 7, 8

		FCT540CT/FCT541CT				FCT540DT/ FCT541DT			
		Milit	ary	Comm	ercial	Comm	ercial		Fig
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Fig. No. ^[13]
t _{PLH} t _{PHL}	Propagation Delay Data to Output (FCT540)	1.5	4.7	1.5	4.1	1.5	3.8	ns	1, 2
t _{PLH} t _{PHL}	Propagation Delay Data to Output (FCT541)	1.5	4.6	1.5	4.1	1.5	3.8	ns	1, 3
t _{PZH} t _{PZL}	Output Enable Time	1.5	6.5	1.5	5.8	1.5	5.2	ns	1, 7, 8
t _{PHZ}	Output Disable Time	1.5	5.7	1.5	5.2	1.5	5.0	ns	1, 7, 8

Shaded areas contain preliminary information.

Minimum limits are specified but not tested on Propagation Delays.
 See "Parameter Measurement Information" in the General Information section.

Ordering Information—FCT540T

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
4.1	CY74FCT540CTQCT	Q5	20-Lead (150-Mil) QSOP	Commercial
4.7	CY54FCT540CTDMB	D6	20-Lead (300-Mil) CerDIP	Military

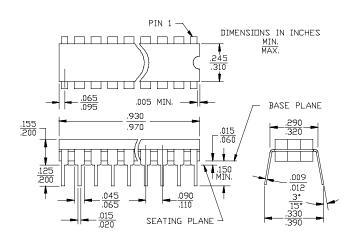
Ordering Information—FCT541T

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
4.1	CY74FCT541CTQCT	Q5	20-Lead (150-Mil) QSOP	Commercial
	CY74FCT541CTSOC/SOCT	S5	20-Lead (300-Mil) Molded SOIC	
4.6	CY54FCT541CTDMB	D6	20-Lead (300-Mil) CerDIP	Military
4.8	CY74FCT541ATPC	P5	20-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT541ATQCT	Q5	20-Lead (150-Mil) QSOP	
	CY74FCT541ATSOC/SOCT	S5	20-Lead (300-Mil) Molded SOIC	
8.0	CY74FCT541TSOC/SOCT	S5	20-Lead (300-Mil) Molded SOIC	Commercial

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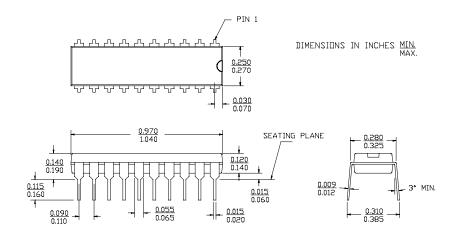
Package Diagrams

20-Lead (300-Mil) CerDIP D6 MIL-STD-1835 D-8 Config.A

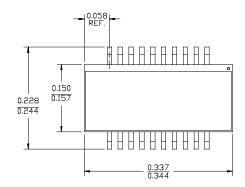


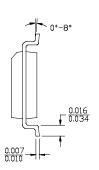
Package Diagrams (continued)

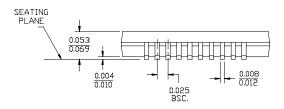
20-Lead (300-Mil) Molded DIP P5



20-Lead Quarter Size Outline Q5



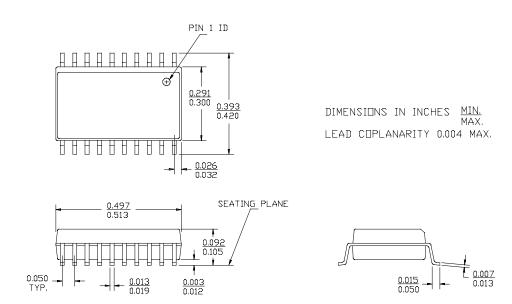




DIMENSIONS IN INCHES $\frac{\text{MIN.}}{\text{MAX.}}$ LEAD COPLANARITY 0.004 MAX.

Package Diagrams (continued)

20-Lead (300-Mil) Molded SOIC S5



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